

Amendments to the Specification

Please replace the paragraph beginning on page 7, line 8 of the Substitute Specification with the following amended paragraph:

In this embodiment, the P-channel transistor 55 and the N-channel transistor 214 are connected in parallel between the sense amplifier 301 and the left bit line BL. Therefore, even if the transistors 55 and 214 are driven by the voltage VDD, the data can be transferred without a voltage drop. When the input node SBL is the "H" level, the N-channel transistor 55 which is driven by the VDD level generates the voltage drop V_t caused by the threshold voltage. At the P-channel transistor 214 which is driven by the GND level, the voltage drop caused by the threshold voltage [[dose]] does not occur when the input node SBL is the "H" level. As a result, the "H" level of the input node SBL in the sense amplifier 301 can be transferred to the bit line BL without the voltage drop. When the input node SBL is the "L" level, the P-channel transistor 214 generates the voltage drop caused by the threshold voltage. However, the N-channel transistor 55 does not generate the voltage drop when the bit line voltage is the "L" level. As a result, the "L" level of the input node SBL in the sense amplifier 301 can be transferred to the bit line BL without the voltage drop.